

IN THE CLAIMS

Please amend Claims 1 and 2, to read as follows.

1. (Currently Amended) A dielectric film structure having a substrate and a dielectric film provided on said substrate, wherein

said dielectric film has ~~(001)~~ (001) face orientation with respect to said substrate; and

a value u in the following equation (1) regarding said dielectric film is a real number greater than 2:

$$u = (C_c/C_a) \times (W_a/W_c) \quad \dots (1)$$

where, C_c is a count number of a peak of a $(00l')$ face of said dielectric film in an Out-of-plane X ray diffraction measurement (here, l' is a natural number selected so that C_c becomes maximum); C_a is a count number of a peak of a $(h'00)$ face of said dielectric film in an In-plane X ray diffraction measurement (here, h' is a natural number selected so that C_c becomes maximum); W_c is a half-value width of a peak of the $(00l')$ face of said dielectric film in an Out-of-plane rocking curve X ray diffraction measurement; and W_a is a half-value width of a peak of the $(h'00)$ face of said dielectric film in an In-plane rocking curve X ray diffraction measurement.

2. (Currently Amended) A dielectric film structure according to claim 1, wherein, in said dielectric film, a count number of faces other than a ~~(001)~~ (001) face is smaller than 10% of a count number of the $(00l')$ face in the Out-of-plane X ray diffraction measurement and a count number of faces other than a $(h00)$ face is smaller than 10% of a count number of the $(h'00)$ face in the In-plane X ray diffraction measurement (here, h

and l are any natural numbers and l' is a natural number selected so that the count number of the peak of the $(00l')$ face becomes maximum in the Out-of-plane X ray diffraction measurement and $[[h]]$ h' is a natural number selected so that the count number of the peak of the $(h'00)$ face becomes maximum in the In-plane X ray diffraction measurement).

3. (Original) A dielectric film structure according to claim 1, wherein a thickness of said dielectric film is greater than 10 nm and smaller than 20 μm .

4. (Original) A dielectric structure according to claim 1, wherein a crystal structure of said dielectric film is square crystal.

5. (Canceled)

6. (Canceled)

7. (Original) A dielectric structure according to claim 1, wherein a crystal structure of said dielectric film is rhombic crystal.

8. (Canceled)

9. (Canceled)

10. (Original) A piezoelectric actuator comprising:
a dielectric film structure according to claim 1; and
an electrode for applying voltage to said dielectric film structure.

11. (Canceled)

12. (Canceled)

13. (Original) An ink jet head comprising:
a piezoelectric actuator including a dielectric film structure according to claim 1
and an electrode for applying voltage to said dielectric film structure, and wherein said
piezoelectric actuator is driven to discharge ink.

14. (Canceled)

15. (Canceled)